NSN 5962-01-357-6614



Memory Microcircuit - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5962-01-357-6614 **Body Length:** 1.060 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** Between 0.130 inches and 0.185 inches **Maximum Power Dissipation Rating:** 2.0 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius **Features Provided:** Bidirectional and bipolar and programmable and high impedance and w/clock and w/disable and monolithic **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 16 input **Case Outline Source And Designator:** D-8 mil-m-38510 **Current Rating Per Characteristic:** 180.00 milliamperes reverse current, dc absolute **Terminal Surface Treatment:** Solder **Product Name:** And/or invert gate array Voltage Rating And Type Per Characteristic: -0.5 volts power source and 12.0 volts power source **Time Rating Per Chacteristic:**

30.00 nanoseconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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